## CHANGE NOTIFICATION



June 03, 2015

Dear Sir/Madam: PCN# 060315

## Subject: Notification of Change to LTC4232-1 Datasheet

Please be advised that Linear Technology Corporation has made a minor change to the LTC4232-1 product datasheet to facilitate improvement in our manufacturing yield. The change is shown on the attached page of the marked up datasheet. There was no change made to the die. The product shipped after August 03, 2015 will be tested to the new limits.

Should you have any further questions or concerns please contact your local Linear Technology Sales person or you may contact me at 408-432-1900 ext. 2077, or by e-mail at <a href="mailto:jason.hu@linear.com">jason.hu@linear.com</a>. If I do not hear from you by August 03, 2015, we will consider this change to be approved by your company.

Sincerely,

Jason Hu Quality Assurance Engineer

## **ELECTRICAL CHARACTERISTICS** The ullet denotes those specifications which apply over the full operating temperature range, otherwise specifications are at $T_A = 25^{\circ}\text{C}$ . $V_{DD} = 12\text{V}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
Inputs							
I <sub>IN</sub>	OV, UV, FB Pin Input Current	V = 1.2V	•		0	±1	μА
V <sub>TH</sub>	OV, UV, FB Pin Threshold Voltage	V <sub>PIN</sub> Rising	•	1.21	1.235	1.26	V
ΔV <sub>OV(HYST)</sub>	OV Pin Hysteresis		•	10	20	30	mV
ΔV <sub>UV(HYST)</sub>	UV Pin Hysteresis		•	50	80	110	mV
V <sub>UV(RTH)</sub>	UV Pin Reset Threshold Voltage	V <sub>UV</sub> Falling	•	0.55	0.62	0.7	V
ΔV <sub>FB(HYST)</sub>	FB Pin Power Good Hysteresis		•	10	20	30	mV
RISET	I <sub>SET</sub> Pin Internal Resistor		•	19	20	21	kΩ
Outputs							
VINTVCC	INTV <sub>CC</sub> Output Voltage	V <sub>DD</sub> = 5V, 15V, I <sub>LOAD</sub> = 0mA, -10mA	•	2.8	3.1	3.3	V
V <sub>OL</sub>	PG, FLT Pin Output Low Voltage	I = 2mA	•		0.4	8.0	V
ОН	PG, FLT Pin Input Leakage Current	V = 30V	•		0	±10	μА
V <sub>TIMER(H)</sub>	TIMER Pin High Threshold	V <sub>TIMER</sub> Rising	•	1.2	1.235	1.28	V
V <sub>TIMER(L)</sub>	TIMER Pin Low Threshold	V <sub>TIMER</sub> Falling	•	0.1	0.21	0.3	V
TIMER(UP)	TIMER Pin Pull-Up Current	V <sub>TIMER</sub> = 0V	•	-80	-100	-120	μА
TIMER(DN)	TIMER Pin Pull-Down Current	V <sub>TIMER</sub> = 1.2V	•	1.4	2	2.6	μА
I <sub>TIMER(RATIO)</sub>	TIMER Pin Current Ratio I <sub>TIMER(DN)</sub> /I <sub>TIMER(UP)</sub>		•	1.6	2	2.7	%
A <sub>IMON</sub>	I <sub>MON</sub> Pin Current Gain	I <sub>OUT</sub> = 2.5A	•	18.5	20	21.5	μA/A
I <sub>OFF(IMON)</sub>	I <sub>MON</sub> Pin Offset Current	I <sub>OUT</sub> = 150mA	•		0	±4.5	μА
I <sub>GATE(UP)</sub>	Gate Pull-Up Current	Gate Drive On, V <sub>GATE</sub> = V <sub>OUT</sub> = 12V	•	-18	-24	-29	μА
I <sub>GATE(DN)</sub>	Gate Pull-Down Current	Gate Drive Off, V <sub>GATE</sub> = 18V, V <sub>OUT</sub> = 12V	•	180	250	400 <del>-340-</del>	μΑ
I <sub>GATE(FST)</sub>	Gate Fast Pull-Down Current	Fast Turn Off, V <sub>GATE</sub> = 18V, V <sub>OUT</sub> = 12V			140		mA
AC Characteris	etics						
t <sub>PHL(GATE)</sub>	Input High (OV), Input Low (UV) to Gate Low Propagation Delay	V <sub>GATE</sub> < 16.5V Falling	•		8	10	μs
t <sub>PHL(ILIM)</sub>	Short-Circuit to Gate Low	V <sub>FB</sub> = 0, Step I <sub>SENSE</sub> to 6A, V <sub>GATE</sub> < 15V Falling	•		1	5	μs
t <sub>D(ON)</sub>	Turn-On Delay	Step V <sub>UV</sub> to 2V, V <sub>GATE</sub> > 13V	•	8	16	24	ms
t <sub>D(CB)</sub>	Circuit Breaker Filter Delay Time (Internal)	V <sub>FB</sub> = OV, Step I <sub>SENSE</sub> to 3A.	•	1.3	2	2.7	ms
t <sub>D(AUTO-RETRY)</sub>	Auto-Retry Turn-On Delay (Internal)		•	8	16	24	ms

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

Note 2: All currents into pins are positive, all voltages are referenced to GND unless otherwise specified.

Note 3: An internal clamp limits the GATE pin to a maximum of 6.5V above OUT. Driving this pin to voltages beyond the clamp may damage the device.

Note 4: This IC includes overtemperature protection that is intended to protect the device during momentary overload conditions. Junction temperature will exceed 125°C when overtemperature protection is active. Continuous operation above the specified maximum operating junction temperature may impair device reliability.

Note 5:  $T_J$  is calculated from the ambient temperature,  $T_A$ , and power dissipation,  $P_D$ , according to the formula:

$$T_J = T_A + (P_D \cdot 43^{\circ}C/W)$$

